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CORRECTION

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Correction: A weakened Fermi level pinning induced adsorption energy non-charge-transfer mechanism during O_2 adsorption in silicene/graphene heterojunctions

Xuhong Zhao, Haiyuan Chen, Jianwei Wang* and Xiaobin Niu*

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Correction for 'A weakened Fermi level pinning induced adsorption energy non-charge-transfer mechanism during O_2 adsorption in silicene/graphene heterojunctions' by Xuhong Zhao *et al.*, *Phys. Chem. Chem. Phys.*, 2024, **26**, 3525–3530, https://doi.org/10.1039/D3CP05139K.

The authors would like to correct an error in the caption of Fig. 4 of the published article. The caption of Fig. 4(d) in the published version contains inaccuracies in the description of the PDOS (Projected Density of States). Correct results are shown here. These changes do not affect the conclusions or text of the original article.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

School of Materials and Energy, University of Electronic Science and Technology of China, Xiyuan Avenue, Chengdu, 611731, China. E-mail: jianwei_wang@uestc.edu.cn, xbniu@uestc.edu.cn

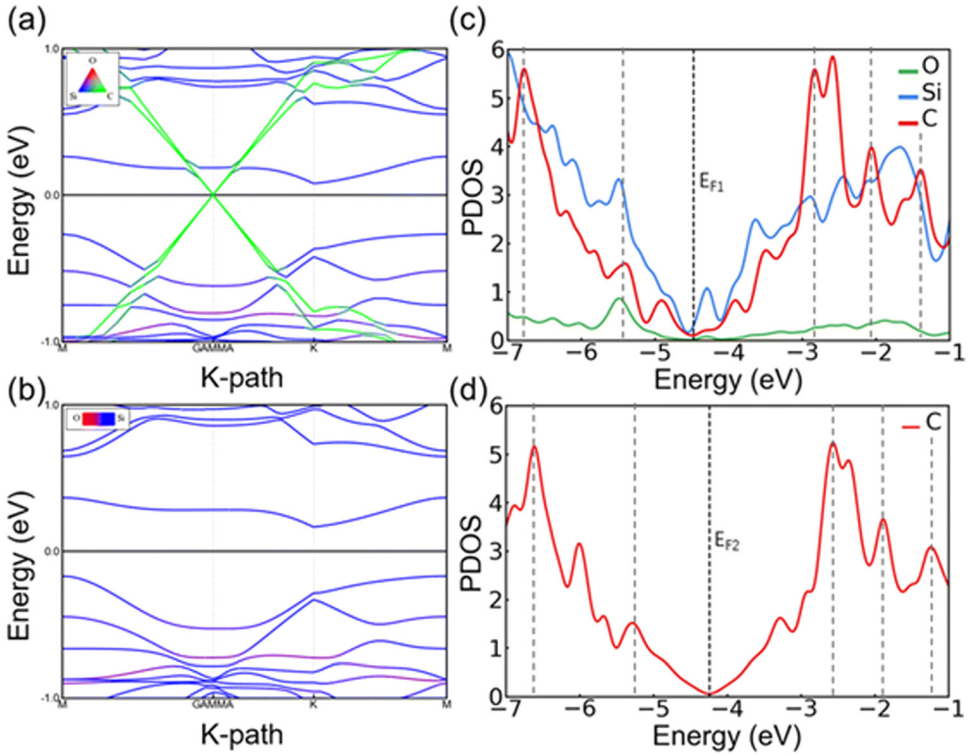

Fig. 4 Energy band structures of the SGH (a) and PS (b) after adsorbing oxygen. The PDOS of the oxygen-absorbing SGH (c) and pure graphene (d) are shown in sequence.